BAS40P

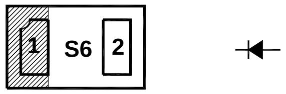
Silicon Epitaxial Planar Schottky Barrier Diode

Features

- Low forward voltage
- Fast switching

PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode



Transparent top view
Marking Code: S6
Simplified outline DFN1006-2H and symbol

Absolute Maximum Ratings (T_a = 25℃)

Parameter	Symbol	Value	Unit
Repetitive Peak Reverse Voltage	V_{RRM}	40	V
DC Blocking Voltage	V_R	40	V
Forward Continuous Current	I_F	200	mA
Peak Forward Surge Current (at tp = 8.3 ms)	I_{FSM}	600	mA
Junction Temperature	T_J	150	℃
Storage Temperature Range	T_{Stg}	- 55 to + 150	℃

Characteristics at T_a = 25℃

Parameter	Symbol	Min.	Max.	Unit
Reverse Breakdown Voltage at I_R = 10 µA	$V_{(BR)R}$	40	-	V
Forward Voltage at I_F = 1 mA at I_F = 40 mA	 V_F V_F	 - -	 0.38 1	 V V
Reverse Current at V_R = 30 V	I_R	-	200	nA
Reverse Recovery Time at I_F = I_R = 10 mA to I_R = 1 mA, R_L = 100 Ω	t_{rr}	-	5	ns
Capacitance at V_R = 0 V, f = 1 MHz	C_j	-	5	pF

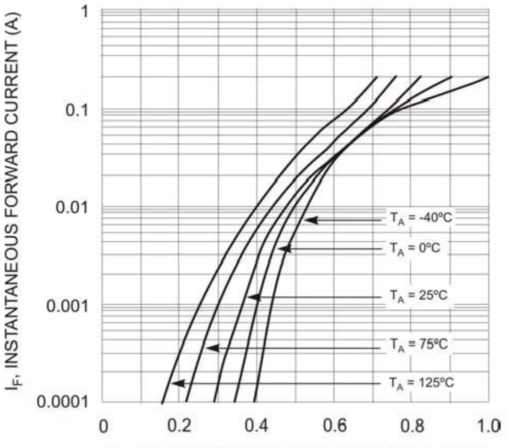


Fig. 1 Typical Forward Voltage

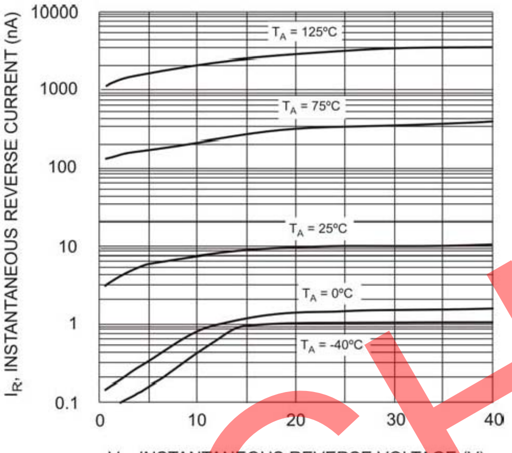


Fig. 2 Typical Reverse Characteristics

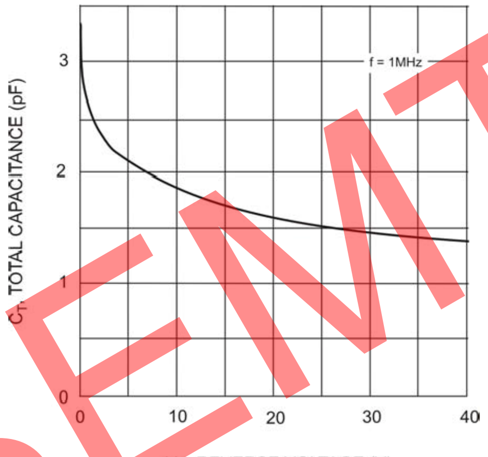
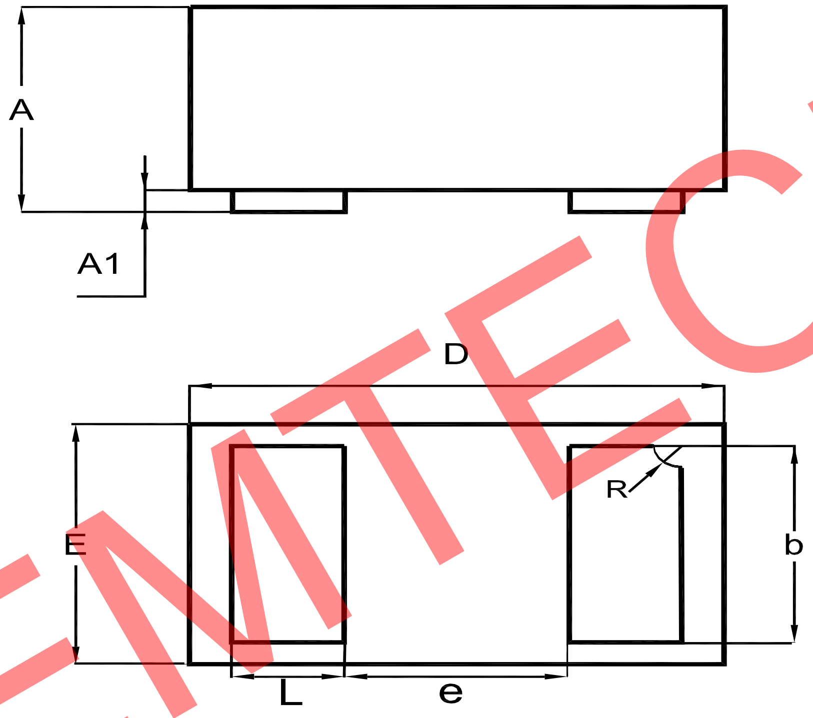


Fig. 3 Typical Capacitance

PACKAGE OUTLINE

Plastic surface mounted package; 2 leads **DFN1006-2H**



UNIT	A	A1	b	D	E	e	L	R
mm	0.51 0.46	0.05 0	0.55 0.45	1.075 0.95	0.675 0.55	0.4	0.3 0.2	0.15 0.05